

# Bobo Tian

## List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

50  
papers

965  
citations

16  
h-index

30  
g-index

55  
ext. papers

1,306  
ext. citations

6  
avg, IF

4.39  
L-index

#	Paper	IF	Citations
50	Programmable transition metal dichalcogenide homojunctions controlled by nonvolatile ferroelectric domains. <i>Nature Electronics</i> , <b>2020</b> , 3, 43-50	28.4	98
49	Size Effect on Optical and Photocatalytic Properties in BiFeO <sub>3</sub> Nanoparticles. <i>Journal of Physical Chemistry C</i> , <b>2016</b> , 120, 3595-3601	3.8	93
48	A Robust Artificial Synapse Based on Organic Ferroelectric Polymer. <i>Advanced Electronic Materials</i> , <b>2019</b> , 5, 1800600	6.4	81
47	Ferroelectric FET for nonvolatile memory application with two-dimensional MoSe <sub>2</sub> channels. <i>2D Materials</i> , <b>2017</b> , 4, 025036	5.9	63
46	Optoelectronic Properties of Few-Layer MoS <sub>2</sub> FET Gated by Ferroelectric Relaxor Polymer. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2016</b> , 8, 32083-32088	9.5	60
45	Research progress on solutions to the sneak path issue in memristor crossbar arrays. <i>Nanoscale Advances</i> , <b>2020</b> , 2, 1811-1827	5.1	55
44	Characterization and Application of PVDF and Its Copolymer Films Prepared by Spin-Coating and Langmuir-Blodgett Method. <i>Polymers</i> , <b>2019</b> , 11,	4.5	47
43	Solid-State Synapse Based on Magnetoelectrically Coupled Memristor. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 5649-5656	9.5	41
42	Graphene/ferroelectric transistors as complementary synapses for supervised learning in spiking neural network. <i>Npj 2D Materials and Applications</i> , <b>2019</b> , 3,	8.8	39
41	Transition of the polarization switching from extrinsic to intrinsic in the ultrathin polyvinylidene fluoride homopolymer films. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 182907	3.4	37
40	Two-Dimensional Ferroelectric Tunnel Junction: The Case of Monolayer In:SnSe/SnSe/Sb:SnSe Homostructure. <i>ACS Applied Electronic Materials</i> , <b>2019</b> , 1, 1133-1140	4	34
39	A High-Speed and Low-Power Multistate Memory Based on Multiferroic Tunnel Junctions. <i>Advanced Electronic Materials</i> , <b>2018</b> , 4, 1700560	6.4	25
38	Flexible Vertical Photogating Transistor Network with an Ultrashort Channel for In-Sensor Visual Nociceptor. <i>Advanced Functional Materials</i> , <b>2021</b> , 31, 2104327	15.6	25
37	Space-charge Effect on Electroresistance in Metal-Ferroelectric-Metal capacitors. <i>Scientific Reports</i> , <b>2015</b> , 5, 18297	4.9	21
36	Efficient two-terminal artificial synapse based on a network of functionalized conducting polymer nanowires. <i>Journal of Materials Chemistry C</i> , <b>2019</b> , 7, 9933-9938	7.1	18
35	Ferroelectric Synaptic Transistor Network for Associative Memory. <i>Advanced Electronic Materials</i> , <b>2021</b> , 7, 2001276	6.4	17
34	Flexible graphene field effect transistor with ferroelectric polymer gate. <i>Optical and Quantum Electronics</i> , <b>2016</b> , 48, 1	2.4	14

33	Polarization switching in ultrathin polyvinylidene fluoride homopolymer ferroelectric films. <i>Ferroelectrics</i> , <b>2017</b> , 509, 143-157	0.6	13
32	An air-stable artificial synapse based on a lead-free double perovskite Cs <sub>2</sub> AgBiBr <sub>6</sub> film for neuromorphic computing. <i>Journal of Materials Chemistry C</i> , <b>2021</b> , 9, 5706-5712	7.1	13
31	Ferroelectric polarization-controlled resistive switching in BaTiO <sub>3</sub> /SmNiO <sub>3</sub> epitaxial heterostructures. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 102901	3.4	11
30	Ultra-wide temperature electronic synapses based on self-rectifying ferroelectric memristors. <i>Nanotechnology</i> , <b>2019</b> , 30, 464001	3.4	10
29	Artificial Synapse Based on Organic-Inorganic Hybrid Perovskite with Electric and Optical Modulation. <i>Advanced Electronic Materials</i> , <b>2021</b> , 7, 2100291	6.4	10
28	Mediation in the second-order synaptic emulator with conductive atomic force microscopy. <i>Nanoscale</i> , <b>2019</b> , 11, 8744-8751	7.7	9
27	Ferroelectric control of magnetism in P(VDF-TrFE)/Co heterostructure. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2015</b> , 26, 7502-7506	2.1	9
26	Nonvolatile Negative Optoelectronic Memory Based on Ferroelectric Thin Films. <i>ACS Applied Electronic Materials</i> , <b>2020</b> , 2, 1035-1040	4	9
25	Graphene Dirac point tuned by ferroelectric polarization field. <i>Nanotechnology</i> , <b>2018</b> , 29, 134002	3.4	9
24	Enhanced ferroelectric and dielectric properties of the P(VDF-TrFE)/Ag nanoparticles composite thin films. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2014</b> , 25, 3461-3465	2.1	9
23	Transparent PVDF-TrFE/Graphene Oxide Ultrathin Films with Enhanced Energy Harvesting Performance. <i>ChemistrySelect</i> , <b>2017</b> , 2, 7951-7955	1.8	9
22	Enhanced piezoelectric response in the artificial ferroelectric polymer multilayers. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 222907	3.4	8
21	Ferroelectric photosensor network: an advanced hardware solution to real-time machine vision.. <i>Nature Communications</i> , <b>2022</b> , 13, 1707	17.4	8
20	Ultralow-Power Machine Vision with Self-Powered Sensor Reservoir.. <i>Advanced Science</i> , <b>2022</b> , e2106092	13.6	8
19	Temperature dependence of electronic transport property in ferroelectric polymer films. <i>Applied Surface Science</i> , <b>2014</b> , 316, 497-500	6.7	7
18	Electrical characterization of MoS <sub>2</sub> field-effect transistors with different dielectric polymer gate. <i>AIP Advances</i> , <b>2017</b> , 7, 065121	1.5	7
17	Interfacial memristors in Al-LaNiO heterostructures. <i>Physical Chemistry Chemical Physics</i> , <b>2017</b> , 19, 16960-16968	3.6	6
16	Self-polarization in ultrathin Langmuir-Blodgett polymer films. <i>Thin Solid Films</i> , <b>2014</b> , 551, 171-173	2.2	6

15	The intermediate temperature T* revealed in relaxor polymers. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 222903-4	3.4	4
14	Preparation of La <sub>0.67</sub> Ca <sub>0.23</sub> Sr <sub>0.1</sub> MnO <sub>3</sub> thin films with interesting electrical and magnetic properties via pulsed-laser deposition. <i>Science China: Physics, Mechanics and Astronomy</i> , <b>2017</b> , 60, 1	3.6	3
13	Doping and band gap control at poly(vinylidene fluoride)/graphene interface. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 195303	3	3
12	High temperature coefficient of resistance for a ferroelectric tunnel junction. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 062904	3.4	3
11	Self-assembled non-volatile micro memory arrays of molecular ferroelectrics. <i>Journal of Materials Chemistry C</i> , <b>2020</b> , 8, 16742-16748	7.1	3
10	Wafer-Scale Diisopropylammonium Bromide Films for Low-Power Lateral Organic Ferroelectric Capacitors. <i>Advanced Electronic Materials</i> , <b>2021</b> , 7, 2000778	6.4	3
9	Fully Light-Modulated Organic Artificial Synapse with the Assistance of Ferroelectric Polarization. <i>Advanced Electronic Materials</i> , 2101402	6.4	3
8	Structural, electrical and magnetic properties of (110)-oriented BF-BZT-ST Films. <i>Ceramics International</i> , <b>2018</b> , 44, 9053-9057	5.1	2
7	Preparation and multiferroicity of a novel two-dimensional material NiH <sub>2</sub> SeO <sub>4</sub> . <i>Journal of Materials Chemistry C</i> , <b>2020</b> , 8, 14812-14818	7.1	2
6	Molecular ferroelectric/semiconductor interfacial memristors for artificial synapses. <i>Npj Flexible Electronics</i> , <b>2022</b> , 6,	10.7	2
5	Ferroelectric polymers for neuromorphic computing. <i>Applied Physics Reviews</i> , <b>2022</b> , 9, 021309	17.3	2
4	Single-Crystalline Thin-Film Memory Arrays of Molecular Ferroelectrics with Ultralow Operation Voltages <b>2022</b> , 4, 758-763		1
3	Amorphous ZrO <sub>2</sub> Tunnel Junction Memristor With a Tunneling Electroresistance Ratio Above 400. <i>IEEE Electron Device Letters</i> , <b>2021</b> , 42, 696-699	4.4	0
2	Ferroelectric Synapses: A Robust Artificial Synapse Based on Organic Ferroelectric Polymer (Adv. Electron. Mater. 1/2019). <i>Advanced Electronic Materials</i> , <b>2019</b> , 5, 1970006	6.4	0
1	Confinement effect on coercive field in relaxor terpolymer nanowires. <i>Applied Surface Science</i> , <b>2015</b> , 355, 473-476	6.7	